

MC14012B

B-Suffix Series CMOS Gates

The B Series logic gates are constructed with P and N channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power dissipation and/or high noise immunity is desired.

- Supply Voltage Range = 3.0 Vdc to 18 Vdc
- All Outputs Buffered
- Capable of Driving Two Low-power TTL Loads or One Low-power Schottky TTL Load Over the Rated Temperature Range.
- Double Diode Protection on All Inputs
- Pin-for-Pin Replacements for Corresponding CD4000 Series B Suffix Devices

MAXIMUM RATINGS (Voltages Referenced to V_{SS}) (Note 2.)

Symbol	Parameter	Value	Unit
V_{DD}	DC Supply Voltage Range	-0.5 to +18.0	V
V_{in}, V_{out}	Input or Output Voltage Range (DC or Transient)	-0.5 to $V_{DD} + 0.5$	V
I_{in}, I_{out}	Input or Output Current (DC or Transient) per Pin	± 10	mA
P_D	Power Dissipation, per Package (Note 3.)	500	mW
T_A	Ambient Temperature Range	-55 to +125	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-65 to +150	$^{\circ}\text{C}$
T_L	Lead Temperature (8-Second Soldering)	260	$^{\circ}\text{C}$

2. Maximum Ratings are those values beyond which damage to the device may occur.
3. Temperature Derating:
Plastic "P and D/DW" Packages: - 7.0 mW/ $^{\circ}\text{C}$ From 65 $^{\circ}\text{C}$ To 125 $^{\circ}\text{C}$

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high-impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range $V_{SS} \leq (V_{in} \text{ or } V_{out}) \leq V_{DD}$.

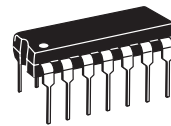
Unused inputs must always be tied to an appropriate logic voltage level (e.g., either V_{SS} or V_{DD}). Unused outputs must be left open.



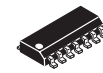
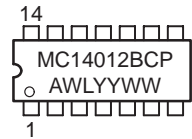
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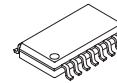
MARKING DIAGRAMS



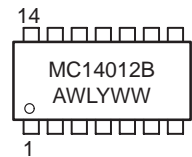
PDIP-14
P SUFFIX
CASE 646



SOIC-14
D SUFFIX
CASE 751A



SOEIAJ-14
F SUFFIX
CASE 965



A = Assembly Location
WL or L = Wafer Lot
YY or Y = Year
WW or W = Work Week

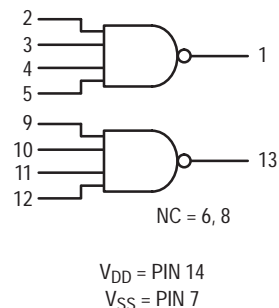
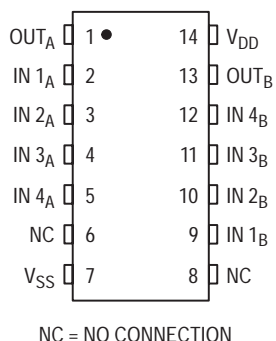
ORDERING INFORMATION

Device	Package	Shipping
MC14012BCP	PDIP-14	2000/Box
MC14012BD	SOIC-14	55/Rail
MC14012BDR2	SOIC-14	2500/Tape & Reel
MC14012BF	SOEIAJ-14	See Note 1.
MC14012BFEL	SOEIAJ-14	See Note 1.

1. For ordering information on the EIAJ version of the SOIC packages, please contact your local ON Semiconductor representative.

MC14012B

MC14012B Dual 4-Input NAND Gate



ELECTRICAL CHARACTERISTICS (Voltages Referenced to V_{SS})

Characteristic	Symbol	V _{DD} Vdc	- 55°C		25°C			125°C		Unit
			Min	Max	Min	Typ ^(4.)	Max	Min	Max	
Output Voltage V _{in} = V _{DD} or 0	"0" Level V _{OL}	5.0	—	0.05	—	0	0.05	—	0.05	Vdc
		10	—	0.05	—	0	0.05	—	0.05	
V _{in} = 0 or V _{DD}	"1" Level V _{OH}	5.0	4.95	—	4.95	5.0	—	4.95	—	Vdc
		10	9.95	—	9.95	10	—	9.95	—	
Input Voltage (V _O = 4.5 or 0.5 Vdc) (V _O = 9.0 or 1.0 Vdc) (V _O = 13.5 or 1.5 Vdc)	"0" Level V _{IL}	5.0	—	1.5	—	2.25	1.5	—	1.5	Vdc
		10	—	3.0	—	4.50	3.0	—	3.0	
(V _O = 0.5 or 4.5 Vdc) (V _O = 1.0 or 9.0 Vdc) (V _O = 1.5 or 13.5 Vdc)	"1" Level V _{IH}	5.0	3.5	—	3.5	2.75	—	3.5	—	Vdc
		10	7.0	—	7.0	5.50	—	7.0	—	
Output Drive Current (V _{OH} = 2.5 Vdc) (V _{OH} = 4.6 Vdc) (V _{OH} = 9.5 Vdc) (V _{OH} = 13.5 Vdc)	Source I _{OH}	5.0	-3.0	—	-2.4	-4.2	—	-1.7	—	mAdc
		5.0	-0.64	—	-0.51	-0.88	—	-0.36	—	
		10	-1.6	—	-1.3	-2.25	—	-0.9	—	
		15	-4.2	—	-3.4	-8.8	—	-2.4	—	
(V _{OL} = 0.4 Vdc) (V _{OL} = 0.5 Vdc) (V _{OL} = 1.5 Vdc)	Sink I _{OL}	5.0	0.64	—	0.51	0.88	—	0.36	—	mAdc
		10	1.6	—	1.3	2.25	—	0.9	—	
		15	4.2	—	3.4	8.8	—	2.4	—	
Input Current	I _{in}	15	—	±0.1	—	±0.00001	±0.1	—	±1.0	μAdc
Input Capacitance (V _{in} = 0)	C _{in}	—	—	—	—	5.0	7.5	—	—	pF
Quiescent Current (Per Package)	I _{DD}	5.0	—	0.25	—	0.0005	0.25	—	7.5	μAdc
		10	—	0.5	—	0.0010	0.5	—	15	
		15	—	1.0	—	0.0015	1.0	—	30	
Total Supply Current ^(5.) ^(6.) (Dynamic plus Quiescent, Per Gate, C _L = 50 pF)	I _T	5.0	I _T = (0.3 μA/kHz) f + I _{DD} /N I _T = (0.6 μA/kHz) f + I _{DD} /N I _T = (0.9 μA/kHz) f + I _{DD} /N							μAdc

4. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

5. The formulas given are for the typical characteristics only at 25°C.

6. To calculate total supply current at loads other than 50 pF:

$$I_T(C_L) = I_T(50 \text{ pF}) + (C_L - 50) \text{ Vfk}$$

where: I_T is in μA (per package), C_L in pF, V = (V_{DD} - V_{SS}) in volts, f in kHz is input frequency, and k = 0.001 x the number of exercised gates per package.

MC14012B

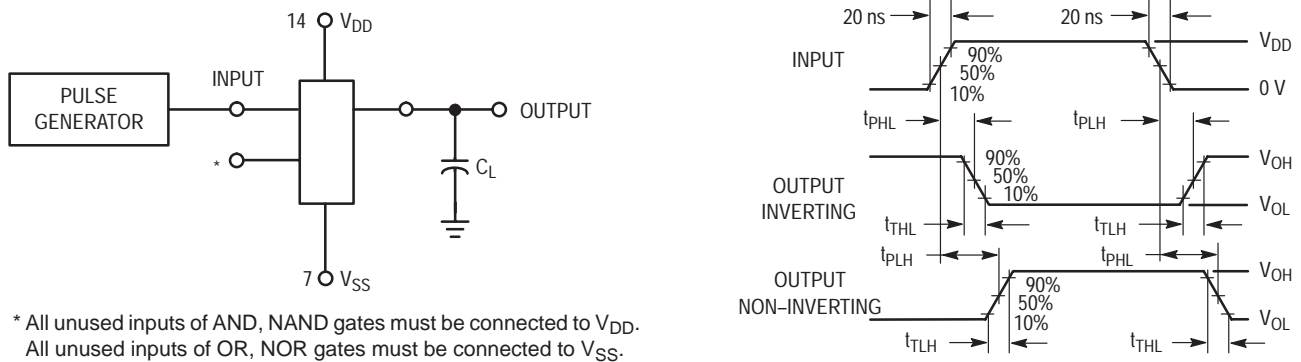
B-SERIES GATE SWITCHING TIMES

SWITCHING CHARACTERISTICS (7.) ($C_L = 50 \text{ pF}$, $T_A = 25^\circ\text{C}$)

Characteristic	Symbol	V_{DD} Vdc	Min	Typ (8.)	Max	Unit
Output Rise Time $t_{TLH} = (1.35 \text{ ns/pF}) C_L + 33 \text{ ns}$ $t_{TLH} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{TLH} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$	t_{TLH}	5.0 10 15	— — —	100 50 40	200 100 80	ns
Output Fall Time $t_{THL} = (1.35 \text{ ns/pF}) C_L + 33 \text{ ns}$ $t_{THL} = (0.60 \text{ ns/pF}) C_L + 20 \text{ ns}$ $t_{THL} = (0.40 \text{ ns/pF}) C_L + 20 \text{ ns}$	t_{THL}	5.0 10 15	— — —	100 50 40	200 100 80	ns
Propagation Delay Time $t_{PLH}, t_{PHL} = (0.90 \text{ ns/pF}) C_L + 115 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.36 \text{ ns/pF}) C_L + 47 \text{ ns}$ $t_{PLH}, t_{PHL} = (0.26 \text{ ns/pF}) C_L + 37 \text{ ns}$	t_{PLH}, t_{PHL}	5.0 10 15	— — —	160 65 50	300 130 100	ns

7. The formulas given are for the typical characteristics only at 25°C .

8. Data labelled "Typ" is not to be used for design purposes but is intended as an indication of the IC's potential performance.

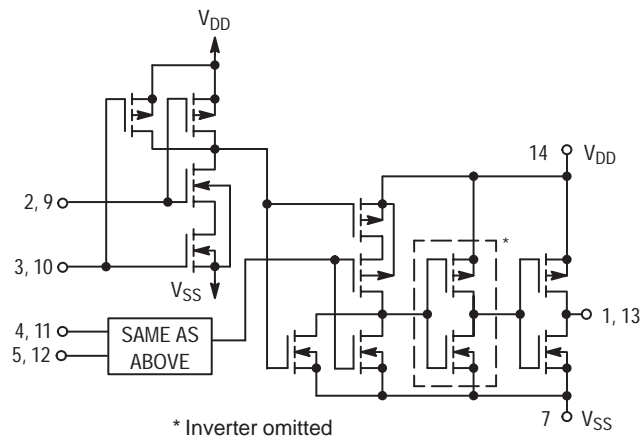


* All unused inputs of AND, NAND gates must be connected to V_{DD} .
 All unused inputs of OR, NOR gates must be connected to V_{SS} .

Figure 1. Switching Time Test Circuit and Waveforms

CIRCUIT SCHEMATIC

MC14012B
 One of Two Gates Shown



TYPICAL B-SERIES GATE CHARACTERISTICS

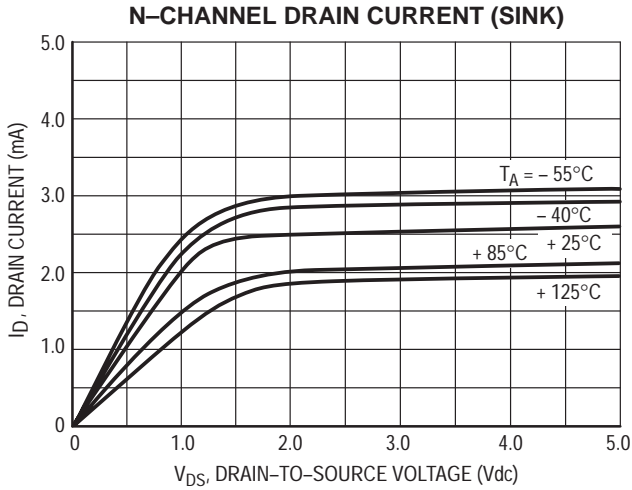


Figure 2. $V_{GS} = 5.0$ Vdc

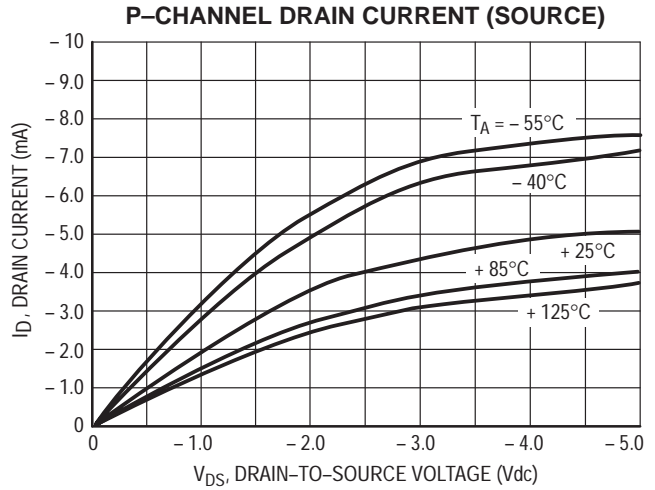


Figure 3. $V_{GS} = -5.0$ Vdc

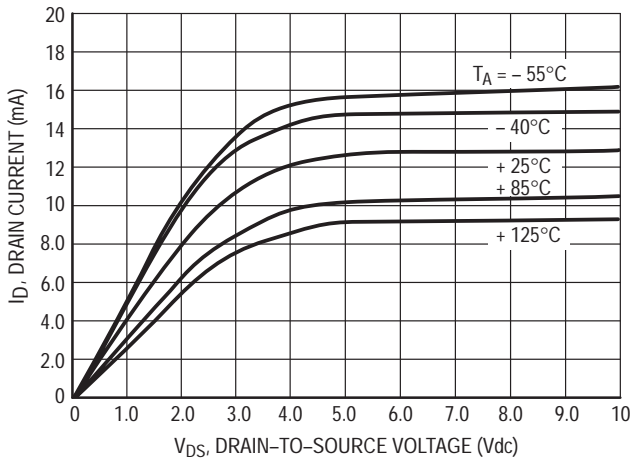


Figure 4. $V_{GS} = 10$ Vdc

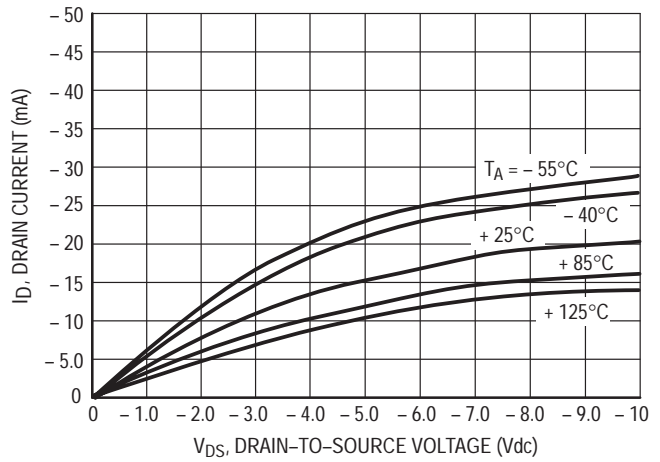


Figure 5. $V_{GS} = -10$ Vdc

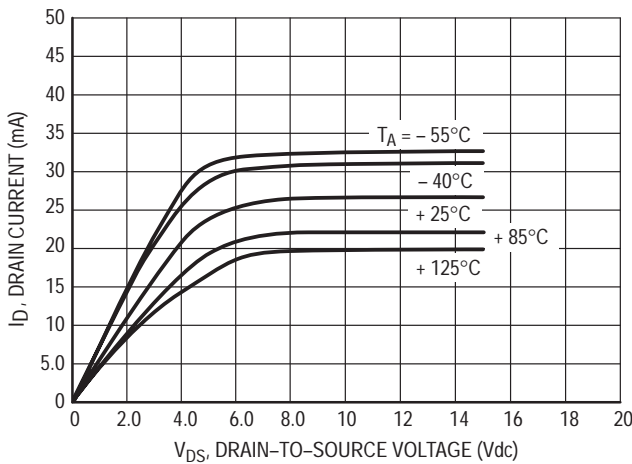


Figure 6. $V_{GS} = 15$ Vdc

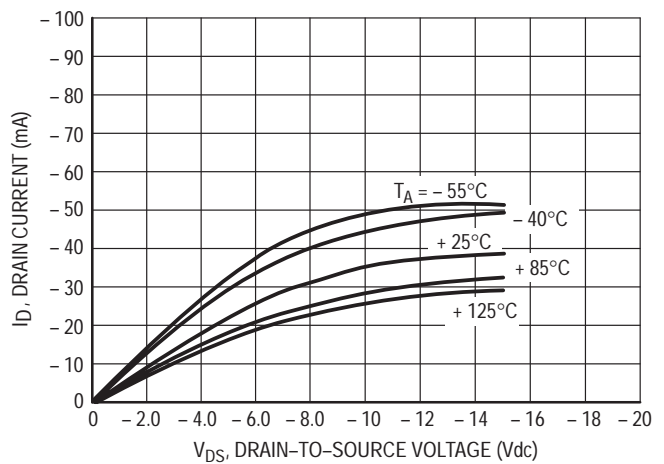


Figure 7. $V_{GS} = -15$ Vdc

These typical curves are not guarantees, but are design aids.
 Caution: The maximum rating for output current is 10 mA per pin.

TYPICAL B-SERIES GATE CHARACTERISTICS (cont'd)

VOLTAGE TRANSFER CHARACTERISTICS

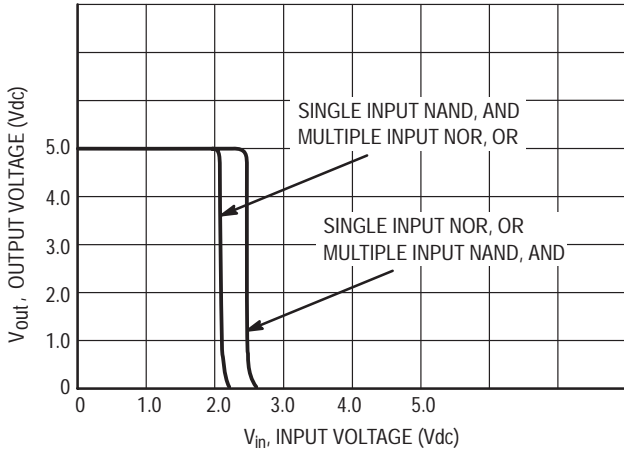


Figure 8. $V_{DD} = 5.0$ Vdc

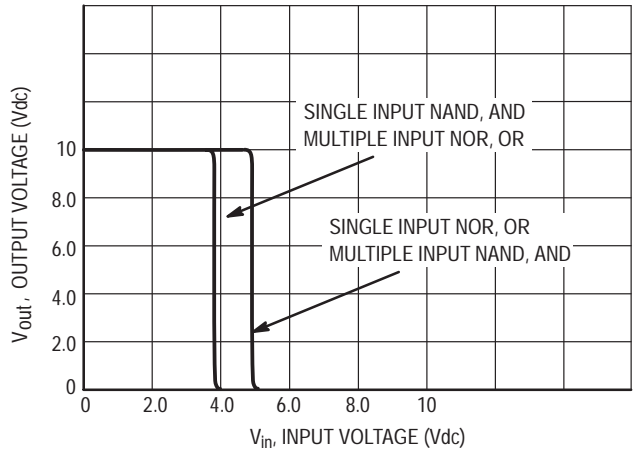


Figure 9. $V_{DD} = 10$ Vdc

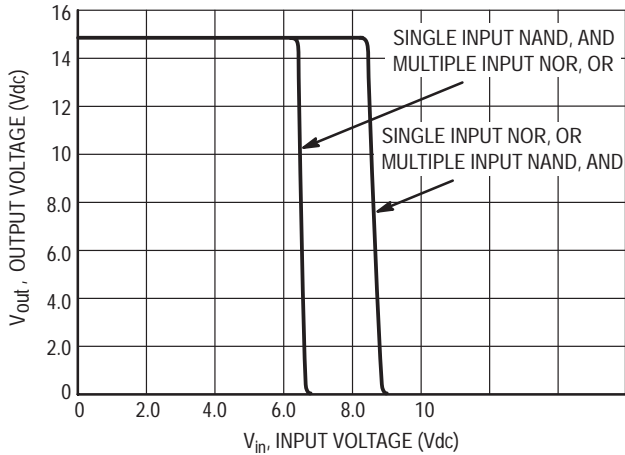


Figure 10. $V_{DD} = 15$ Vdc

DC NOISE MARGIN

The DC noise margin is defined as the input voltage range from an ideal “1” or “0” input level which does not produce output state change(s). The typical and guaranteed limit values of the input values V_{IL} and V_{IH} for the output(s) to be at a fixed voltage V_O are given in the Electrical Characteristics table. V_{IL} and V_{IH} are presented graphically in Figure 11.

Guaranteed minimum noise margins for both the “1” and “0” levels =

- 1.0 V with a 5.0 V supply
- 2.0 V with a 10.0 V supply
- 2.5 V with a 15.0 V supply

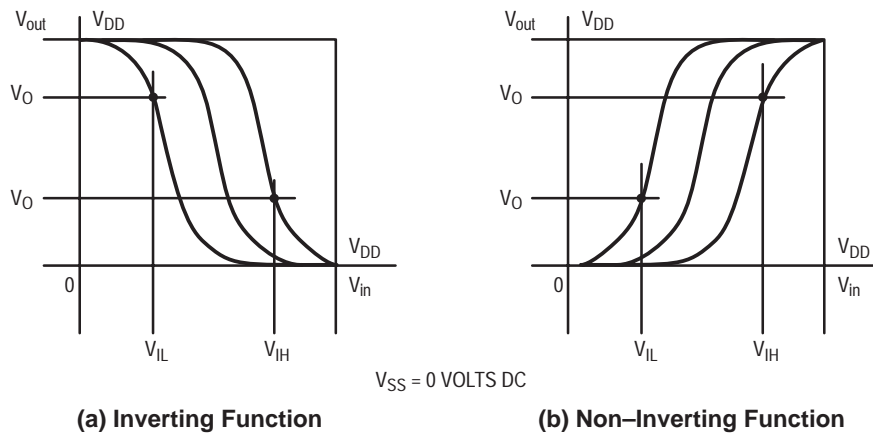


Figure 11. DC Noise Immunity

MC14012B

PACKAGE DIMENSIONS

P SUFFIX PLASTIC DIP PACKAGE CASE 646-06 ISSUE M

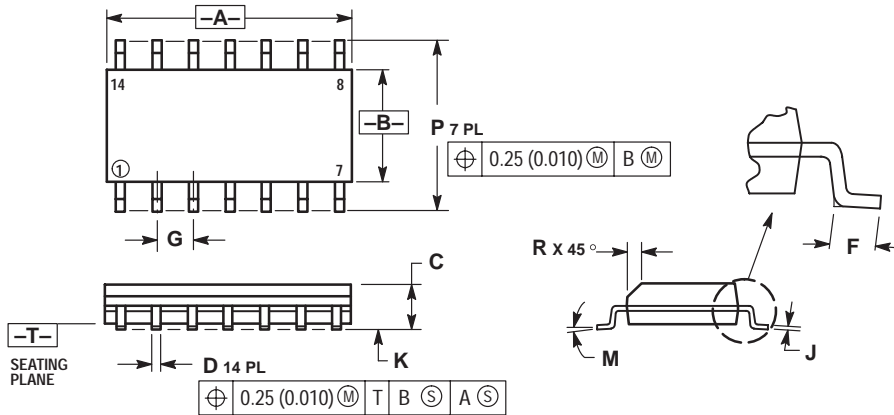


NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION L TO CENTER OF LEADS WHEN FORMED PARALLEL.
4. DIMENSION B DOES NOT INCLUDE MOLD FLASH.
5. ROUNDED CORNERS OPTIONAL.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.715	0.770	18.16	18.80
B	0.240	0.260	6.10	6.60
C	0.145	0.185	3.69	4.69
D	0.015	0.021	0.38	0.53
F	0.040	0.070	1.02	1.78
G	0.100 BSC		2.54 BSC	
H	0.052	0.095	1.32	2.41
J	0.008	0.015	0.20	0.38
K	0.115	0.135	2.92	3.43
L	0.290	0.310	7.37	7.87
M	---	10°	---	10°
N	0.015	0.039	0.38	1.01

D SUFFIX PLASTIC SOIC PACKAGE CASE 751A-03 ISSUE F



NOTES:

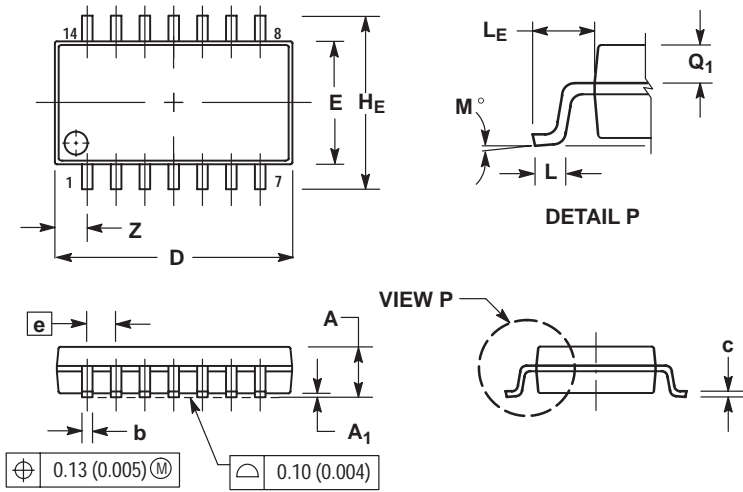
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS A AND B DO NOT INCLUDE MOLD PROTRUSION.
4. MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE.
5. DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	8.55	8.75	0.337	0.344
B	3.80	4.00	0.150	0.157
C	1.35	1.75	0.054	0.068
D	0.35	0.49	0.014	0.019
F	0.40	1.25	0.016	0.049
G	1.27 BSC		0.050 BSC	
J	0.19	0.25	0.008	0.009
K	0.10	0.25	0.004	0.009
M	0°	7°	0°	7°
P	5.60	6.20	0.228	0.244
R	0.25	0.50	0.010	0.019

MC14012B

PACKAGE DIMENSIONS

F SUFFIX PLASTIC EIAJ SOIC PACKAGE CASE 965-01 ISSUE O



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS AND ARE MEASURED AT THE PARTING LINE. MOLD FLASH OR PROTRUSIONS SHALL NOT EXCEED 0.15 (0.006) PER SIDE.
4. TERMINAL NUMBERS ARE SHOWN FOR REFERENCE ONLY.
5. THE LEAD WIDTH DIMENSION (b) DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.08 (0.003) TOTAL IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION. DAMBAR CANNOT BE LOCATED ON THE LOWER RADIUS OR THE FOOT. MINIMUM SPACE BETWEEN PROTRUSIONS AND ADJACENT LEAD TO BE 0.46 (0.018).

DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	—	2.05	—	0.081
A ₁	0.05	0.20	0.002	0.008
b	0.35	0.50	0.014	0.020
c	0.18	0.27	0.007	0.011
D	9.90	10.50	0.390	0.413
E	5.10	5.45	0.201	0.215
e	1.27 BSC		0.050 BSC	
H _E	7.40	8.20	0.291	0.323
0.50	0.50	0.85	0.020	0.033
L _E	1.10	1.50	0.043	0.059
M	0°	10°	0°	10°
Q ₁	0.70	0.90	0.028	0.035
Z	—	1.42	—	0.056

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Associated Documents Item	Short Desc	Size
Data Sheet	B-Suffix Series CMOS Gates	177 kb

Device MC14012B
B-Suffix Series CMOS Gates

The B Series logic gates are constructed with P and N channel enhancement mode devices in a single monolithic structure (Complementary MOS). Their primary use is where low power and/or high noise immunity is desired.

Features:

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- All Outputs Buffered
- Capable of Driving Two Low-power TTL Loads or One Schottky TTL Load Over the Rated Temperature Range
- Double Diode Protection on All Inputs
- Pin-for-Pin Replacements for Corresponding CD400 Series Suffix Devices

Orderable Parts

Action	Orderable Part	Short Desc.	Package Desc.	Pin Count	Case Outline	Status
N/A	MC14012BCP	Dual 4-Input NAND Gate	PDIP	14	646-06	Active
N/A	MC14012BD	Dual 4-Input	SOIC	14	751A-03	Active

		NAND Gate				
N/A	MC14012BDR2	Tape and Reel	SOIC	14	751A-03	Acti
N/A	MC14012BF	Dual 4-Input NAND Gate		14	965-01	Acti
N/A	MC14012BFEL	Tape and Reel		14	965-01	Acti

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